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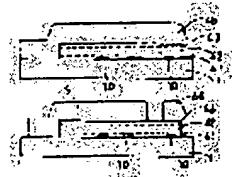
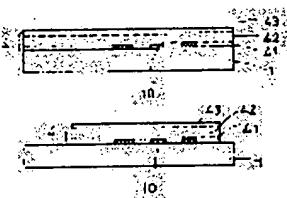
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(54) PHOTODIODE AND MANUFACTURE THEREOF

(57)Abstract:

PURPOSE: To easily obtain a photosensor having high sensitivity without loss of sensitivity at a short wavelength side by arranging pectinated collector electrodes made of a polycrystalline region on one main surface of a translucent substrate, and forming a thin film photosemiconductor layer directly on one main surface of the board by covering the electrode.

CONSTITUTION: A P-type a-SiC layer 41 is formed on an insulating transparent supporting board 1, and recrystallized by laser annealing to form pectinated collector electrode made of polycrystalline SiC. Then, an i-type a-Si layer 42, an n-type a-Si layer 43 are laminated on the layer 41, and a semiconductor film 4 having a pin junction is formed. Thereafter, the film 4 is patterned except a region necessary as a photosensor. Then, a metal film 45 is formed on the film 4. Then, lead electrodes 46 from a back electrode 5 and a collector electrode 10 are formed.



LEGAL STATUS

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